

SEMiX302GAL12E4s



SEMiX® 2s

Trench IGBT Modules

SEMiX302GAL12E4s

Features

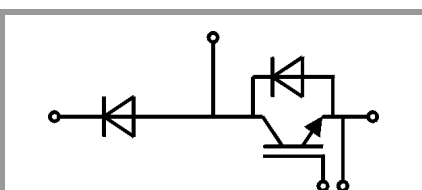
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^{\circ}\text{C}$ max.
- Product reliability results are valid for $T_J=150^{\circ}\text{C}$
- Dynamic values apply to the following combination of resistors:
 $R_{Gon,main} = 0,5 \Omega$
 $R_{Goff,main} = 0,5 \Omega$
 $R_{G,X} = 2,2 \Omega$
 $R_{E,X} = 0,5 \Omega$



GAL

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 175 °C	T _c = 25 °C	463	A
		T _c = 80 °C	356	A
I _{Cnom}			300	A
I _{CRM}	I _{CRM} = 3xI _{Cnom}		900	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 20 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	μs
T _j			-40 ... 175	°C
Inverse diode				
I _F	T _j = 175 °C	T _c = 25 °C	356	A
		T _c = 80 °C	266	A
I _{Fnom}			300	A
I _{FRM}	I _{FRM} = 3xI _{Fnom}		900	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		1620	A
T _j			-40 ... 175	°C
Freewheeling diode				
I _F	T _j = 175 °C	T _c = 25 °C	356	A
		T _c = 80 °C	266	A
I _{Fnom}			300	A
I _{FRM}	I _{FRM} = 3xI _{Fnom}		900	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		1620	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C		600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 300 \text{ A}$ $V_{GE} = 15 \text{ V}$ chipelevel	$T_J = 25^{\circ}\text{C}$	1.8	2.05	V
		$T_J = 150^{\circ}\text{C}$	2.2	2.4	V
V_{CE0}	chipelevel	$T_J = 25^{\circ}\text{C}$	0.8	0.9	V
		$T_J = 150^{\circ}\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15 \text{ V}$ chipelevel	$T_J = 25^{\circ}\text{C}$	3.3	3.8	$\text{m}\Omega$
		$T_J = 150^{\circ}\text{C}$	5.0	5.3	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C = 12 \text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0 \text{ V}$ $V_{CE} = 1200 \text{ V}$	$T_J = 25^{\circ}\text{C}$		4.0	mA
		$T_J = 150^{\circ}\text{C}$			mA
C_{ies}	$V_{CE} = 25 \text{ V}$ $V_{GE} = 0 \text{ V}$	$f = 1 \text{ MHz}$	18.6		nF
C_{oes}	$V_{CE} = 25 \text{ V}$ $V_{GE} = 0 \text{ V}$	$f = 1 \text{ MHz}$	1.16		nF
C_{res}	$V_{CE} = 25 \text{ V}$ $V_{GE} = 0 \text{ V}$	$f = 1 \text{ MHz}$	1.02		nF
Q_G	$V_{GE} = -8 \text{ V...} + 15 \text{ V}$		1700		nC
R_{Gint}	$T_J = 25^{\circ}\text{C}$		2.50		Ω



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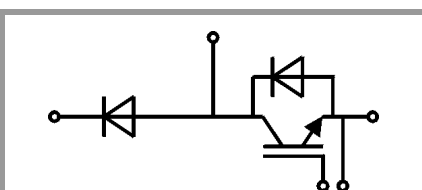
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 $R_{E,X} = 0,5 \Omega$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		282		ns
t _r	I _C = 300 A	T _j = 150 °C		60		ns
E _{on}	V _{GE} = ±15 V	T _j = 150 °C		30		mJ
t _{d(off)}	R _{G on} = 1.9 Ω	T _j = 150 °C		564		ns
t _f	di/dt _{on} = 5000 A/μs	T _j = 150 °C		117		ns
E _{off}	di/dt _{off} = 2800 A/μs	T _j = 150 °C		44		mJ
R _{th(j-c)}	per IGBT				0.096	K/W
Inverse diode						
V _F = V _{EC}	I _F = 300 A	T _j = 25 °C		2.1	2.46	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.1	2.4	V
V _{F0}	chiplevel	T _j = 25 °C	1.1	1.3	1.5	V
		T _j = 150 °C	0.7	0.9	1.1	V
r _F	chiplevel	T _j = 25 °C	2.2	2.8	3.2	mΩ
		T _j = 150 °C	3.3	3.9	4.3	mΩ
I _{RRM}	I _F = 300 A	T _j = 150 °C		230		A
Q _{rr}	di/dt _{off} = 4300 A/μs	T _j = 150 °C		50		μC
E _{rr}	V _{GE} = -15 V	T _j = 150 °C		19		mJ
	V _{CC} = 600 V					
R _{th(j-c)}	per diode				0.17	K/W
Freewheeling diode						
V _F = V _{EC}	I _F = 300 A	T _j = 25 °C		2.1	2.46	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.1	2.4	V
V _{F0}	chiplevel	T _j = 25 °C	1.1	1.3	1.5	V
		T _j = 150 °C	0.7	0.9	1.1	V
r _F	chiplevel	T _j = 25 °C	2.2	2.8	3.2	mΩ
		T _j = 150 °C	3.3	3.9	4.3	mΩ
I _{RRM}	I _F = 300 A	T _j = 150 °C		230		A
Q _{rr}	di/dt _{off} = 4300 A/μs	T _j = 150 °C		50		μC
E _{rr}	V _{GE} = -15 V	T _j = 150 °C		19		mJ
	V _{CC} = 600 V					
R _{th(j-c)}	per diode				0.17	K/W
Module						
L _{CE}				18		nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C		0.7		mΩ
		T _C = 125 °C		1		mΩ
R _{th(c-s)}	per module			0.045		K/W
M _s	to heat sink (M5)		3		5	Nm
M _t		to terminals (M6)	2.5		5	Nm
						Nm
w					250	g
Temperature Sensor						
R ₁₀₀	T _C =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];			3550 ±2%		K



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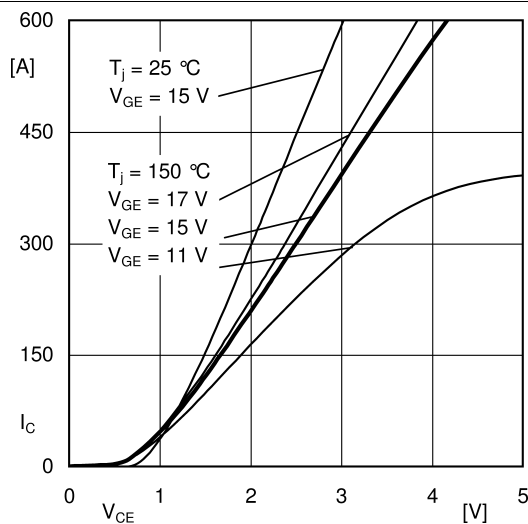


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + E_{E'}$

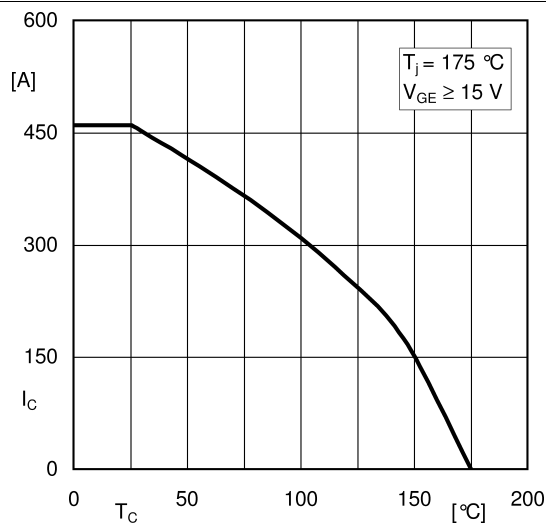


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

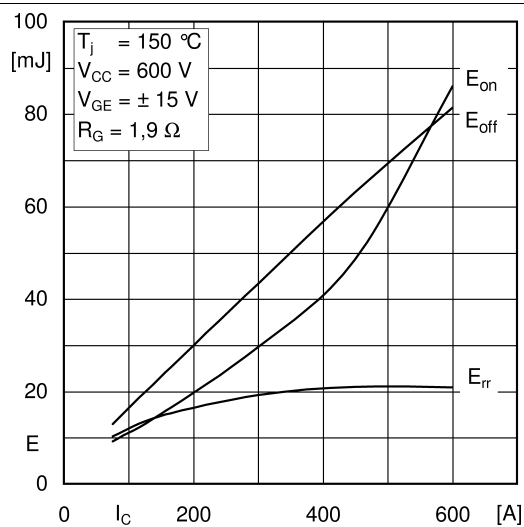


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

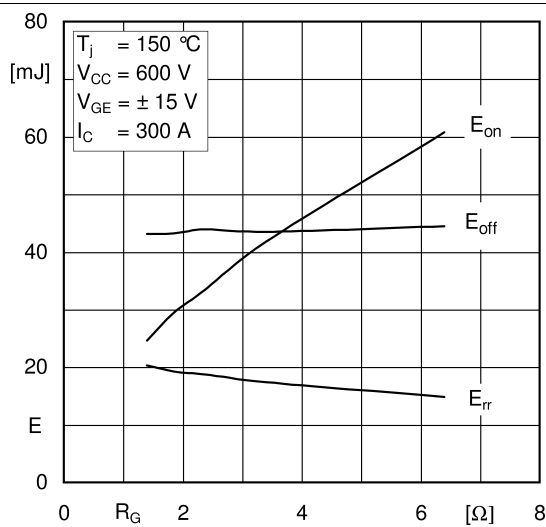


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

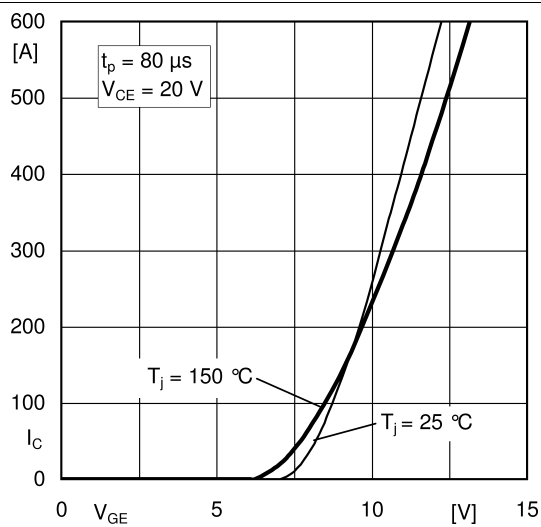


Fig. 5: Typ. transfer characteristic

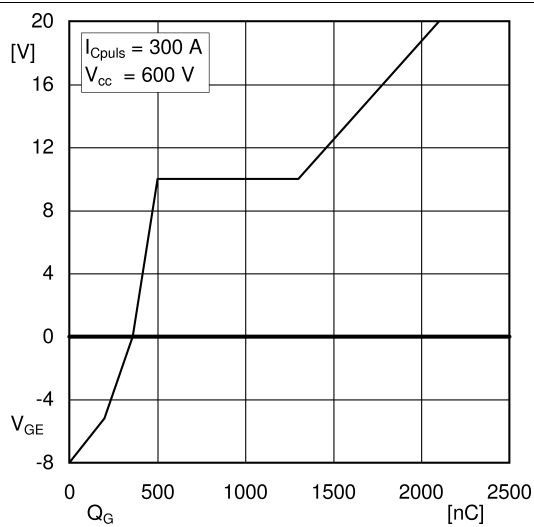
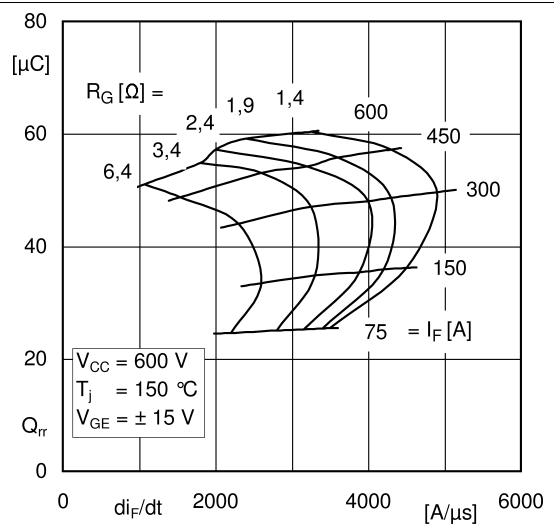
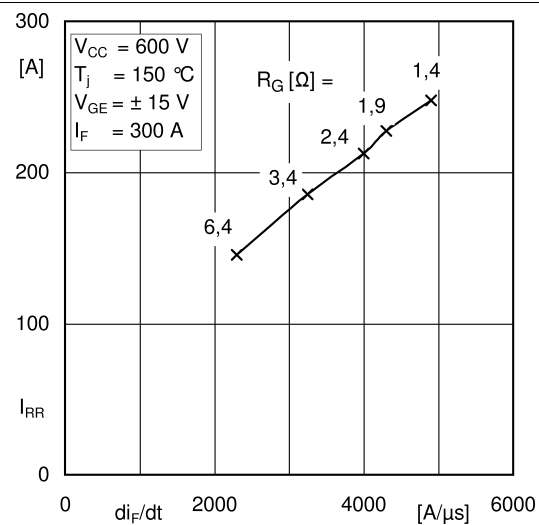
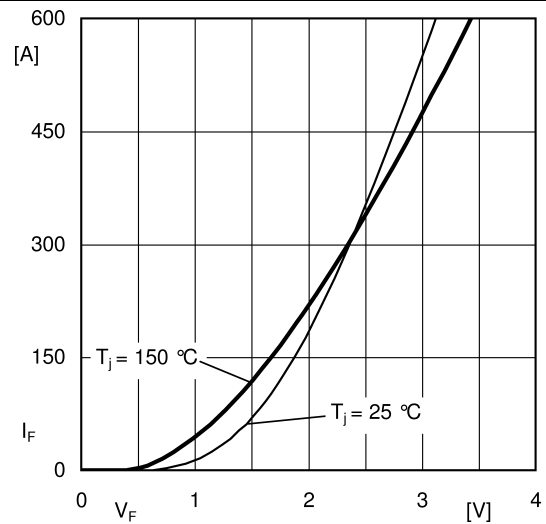
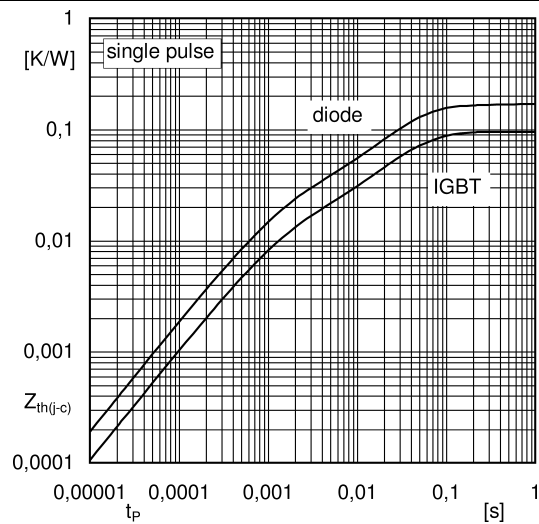
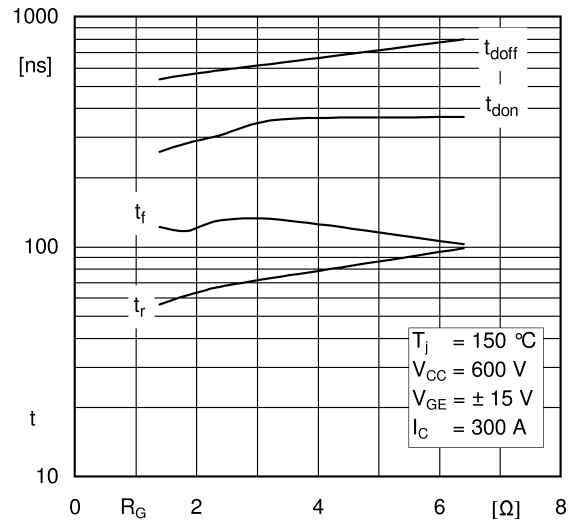
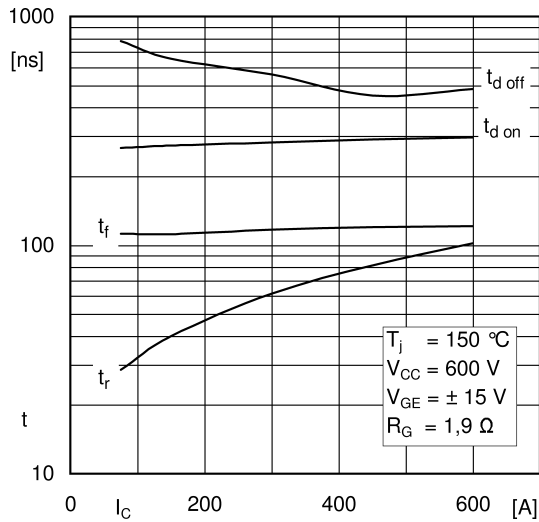
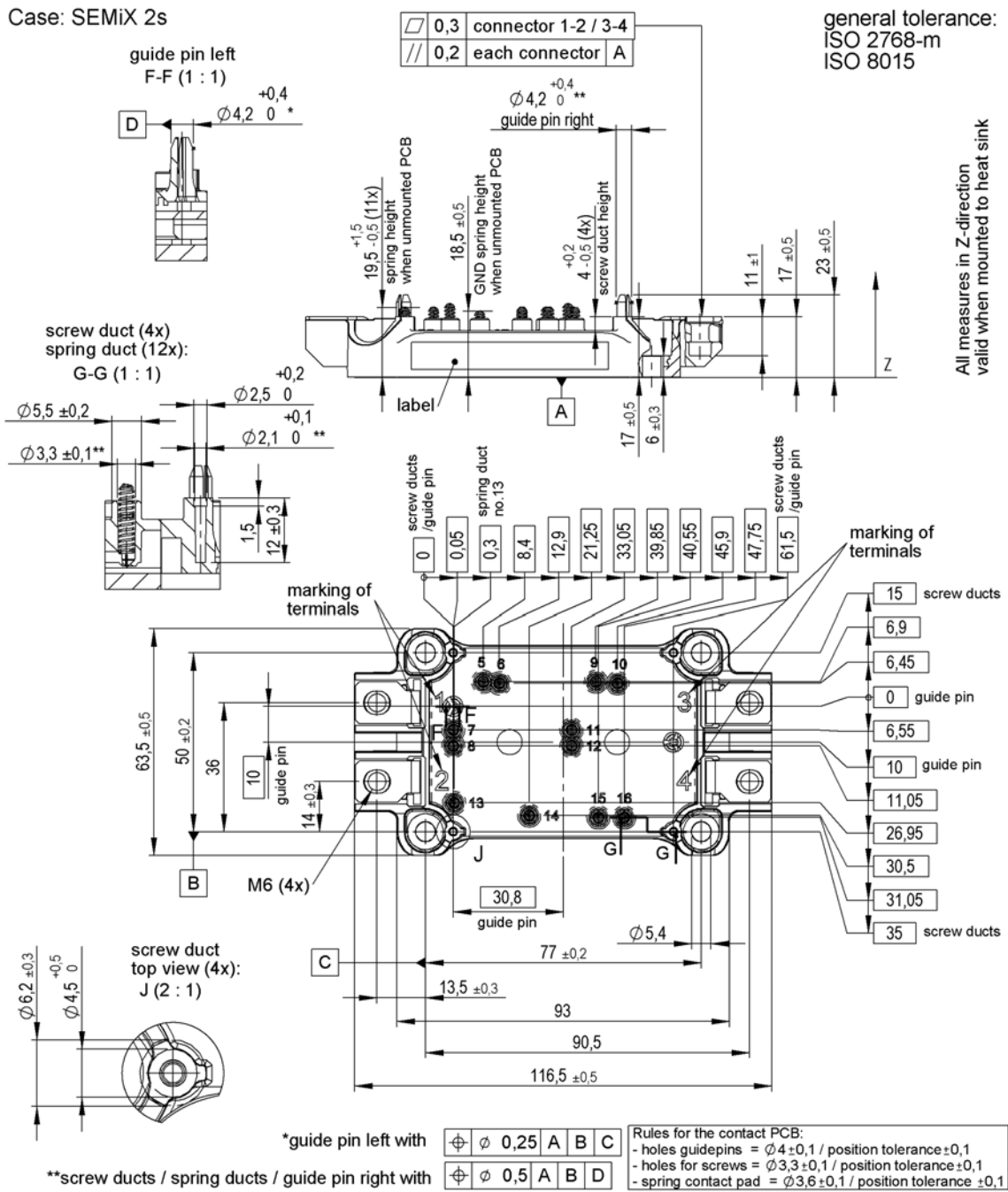


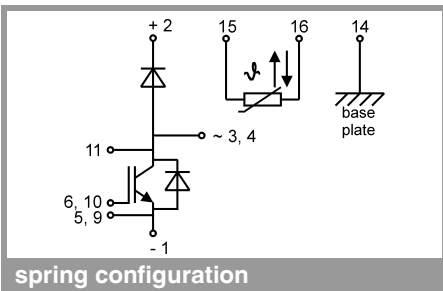
Fig. 6: Typ. gate charge characteristic



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.